

Correction to: Effect of Sintering Temperature on Density and Mechanical Properties of Solid-State Sintered Silicon Carbide Ceramics and Evaluation of Failure Origin

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Readers should note the following corrections to this article:

- (1) Page 4, Fig. 3 caption: SEM micrographs on the polished surfaces of S-SiC sintered at (a) 1950 °C, (b) 2050 °C, (c) 2150 °C and (d) 2180 °C.
- (2) Page 4, Fig. 4 caption: Microstructure of S-SiC sintered at (a) 1950 °C, (b) 2050 °C, (c) 2150 °C and (d) 2180 °C.
- (3) Page 5, Table 2: The numeric value in the second row of third column should be 2046 ± 80 instead of 20.46 ± 80 .

The original article can be found online at <https://doi.org/10.1007/s11665-018-3397-4>.

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